

FLOW RATE CONTROLLER, SUBSTRATE PROCESSING APPARATUS, METHOD OF
MANUFACTURING SEMICONDUCTOR DEVICE, AND PROGRAM

ABSTRACT

A technique includes a valve body rotatably supported about an axis intersecting with a direction of a gas flow in a flow path for a process gas at least partially formed by a pipe, heated to a higher temperature than the pipe, and configured such that an emissivity of at least a portion of a surface of the valve body is set to be equal to or lower than an emissivity of an inner surface of the pipe; and a driver configured to rotate the valve body to change an opening degree of the flow path.

Fig. 5